

NPN SILICON RF-MICROWAVE POWER TRANSISTOR

DESCRIPTION:

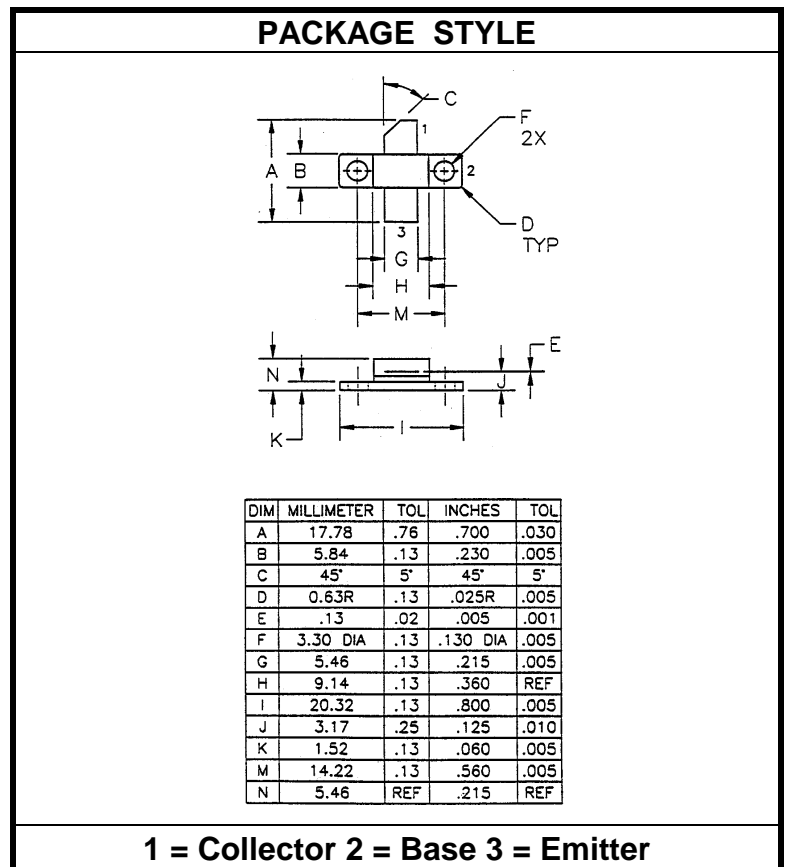
The **ASI TPR175** is a common base transistor Designed for pulsed systems in the frequency band 1030-1090 MHz.

FEATURES:

- Common Base
- Internal Matching Network
- $P_G = 8.0$ dB at 175 W/1090 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	12.5 A
V_{CES}	55 V
V_{EBO}	3.5 V
P_{DISS}	388 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.45 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 20$ mA	55			V
BV_{EBO}	$I_E = 5.0$ mA	3.5			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 20$ mA	10			---
P_G $VSRW$ η_c	$V_{CE} = 50$ V $P_{OUT} = 175$ W $f = 1090$ MHz	8.0	9.0	00:1	dB %
			40		